



isc Silicon NPN Power Transistor

DESCRIPTION

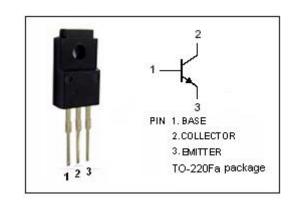
- · Low Collector Saturation Voltage
- · Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

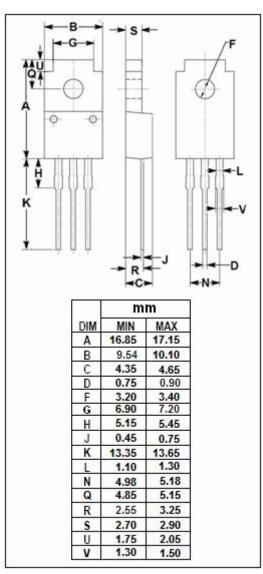
APPLICATIONS

 Designed for high-speed switching, and is ideal for use as a driver in devices such as switching reglators,DC/DC converters, and high frequency power amplifiers.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	12	V
Ic	Collector Current-Continuous	5	Α
I _{CM}	Collector Current-Peak	10	А
I _B	Base Current-Continuous	2.5	Α
Pc	Collector Power Dissipation @ T _a =25℃	1.5	
	Total Power Dissipation @ T _c =25℃	25	W
Тл	Junction Temperature	150	$^{\circ}\!\mathbb{C}$
T _{stg}	Storage Temperature Range	-55~150	°C







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2SC3566

ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO}	Collector-Emitter Sustaining Voltage	I _C = 30mA ; I _B = 0	60		V
V _{CEX(SUS)-1}	Collector-Emitter Sustaining Voltage	I_{C} = 3.0A; I_{B1} =- I_{B2} = 0.3A, $V_{BE(OFF)}$ =5.0V, L=180 μ H,clamped	80		V
V _{CEX(SUS)-2}	Collector-Emitter Sustaining Voltage	I_C = 6.0A; I_{B1} = 0.6A; I_{B2} = -0.3A, $V_{BE(OFF)}$ = -5.0V, L= 180 μ H,clamped	60		V
$V_{\text{CE}(\text{sat})}$	Collector-Emitter Saturation Voltage	I _C = 3.0A; I _B = 0.3A		0.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 3.0A; I _B = 0.3A		1.5	٧
Ісво	Collector Cutoff Current	V _{CB} = 60V; I _E = 0		10	μ А
I _{CER}	Collector Cutoff Current	V _{CE} = 60V; R _{BE} = 51 Ω , T _a =125 °C		1.0	mA
I _{CEX}	Collector Cutoff Current	V _{CE} = 60V; V _{BE(off)} = -1.5V V _{CE} = 60V; V _{BE(off)} = -1.5V, T _a =125°C		10 1.0	μA mA
I_{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C =0		10	μ A
h _{FE-1}	DC Current Gain	I _C = 0.3A; V _{CE} = 5V	40		
h _{FE-2}	DC Current Gain	I _C = 3.0A; V _{CE} = 5V	40	200	
Switching ti	mes				
t _{on}	Turn-on Time			0.5	μS
t _{stg}	Storage Time	I_{C} = 3.0A ,R _L = 17 Ω , I_{B1} = - I_{B2} = 0.3A.V _{CC} \approx 50V		3.0	μ \$
t _f	Fall Time			0.5	μ S

♦ h_{FE-2} Classifications

M	L	K
40-80	60-120	100-200

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